

N-Channel Enhancement Mode MOSFET
Product Information
Features

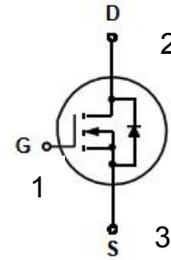
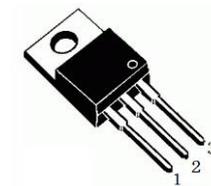
- ◆ Advanced trench cell design
- ◆ Low Thermal Resistance

Applications

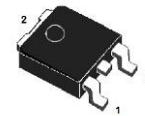
- ◆ Motor drivers
- ◆ DC - DC Converter
- ◆ Automotive applications
- ◆ Uninterruptible power supply

Quick reference

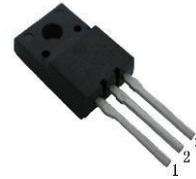
- ◆ $BV \cong 80\text{ V}$
- ◆ $P_{tot} \cong 250\text{ W}$
- ◆ $ID \cong 70\text{ A}$
- ◆ $R_{DS(ON)} \cong 12\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ◆ $R_{DS(ON)} \cong 19\text{ m}\Omega @ V_{GS} = 6\text{ V}$

Symbol

Simplified Outline


TO-220-3L



TO-252-2L



TO-220F-3L

Marking Information


Product Name	Package	Marking	Quantity	RoHS
SR080N08T	TO-220-3L	SR080N08T	50	meet a criterion
SR08N08F	TO-220F-3L	SR08N08F	50	meet a criterion
SR08N08D	TO-252-2L	SR08N08D	3000	meet a criterion

Note: NHCX defines “ Green ” as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	Drain-Source Voltage	T _C = 25 °C	80	-	V
V _{GS}	Gate-Source Voltage	T _C = 25 °C	-	± 20	V
I _D *	Drain Current (DC)	T _C = 25 °C, V _{GS} = 10 V	-	70	A
		T _C = 100 °C, V _{GS} = 10 V	-	50	A
I _{DM} *,**	Drain Current (Pulsed)	T _C = 25 °C, V _{GS} = 10 V	-	280	A
P _{tot} *	Total Power Dissipation	T _C = 25 °C	-	250	W
T _{stg}	Storage Temperature		- 55	150	°C
T _J	Junction Temperature		-	150	°C
I _S	Diode Forward Current	T _C = 25 °C	-	70	A
E _{AS} *	Single Pulsed Avalanche Energy	V _{DD} = 50 V , L = 0.5 mH	-	40	mJ
R _{θJA} *	Thermal Resistance- Junction to Ambient		-	42	°C / W
R _{θJC} *	Thermal Resistance- Junction to Case		-	0.5	

Notes :

- * Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- ** Surface Mounted on 1 in² pad area, t 10 sec
- *** Limited by bonding wire

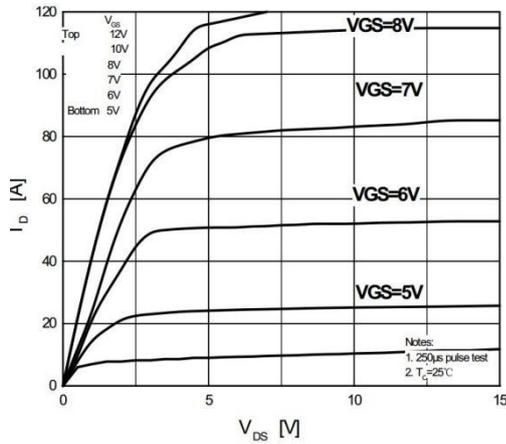
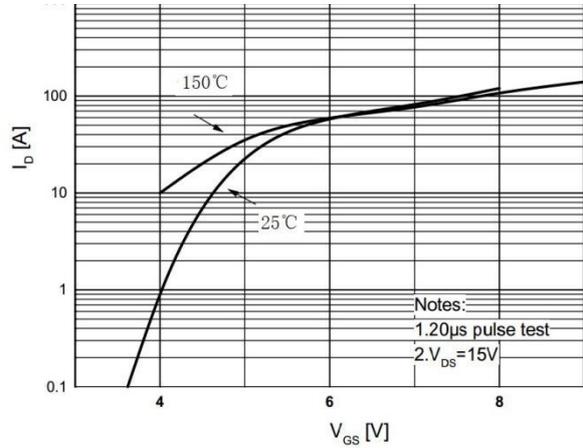
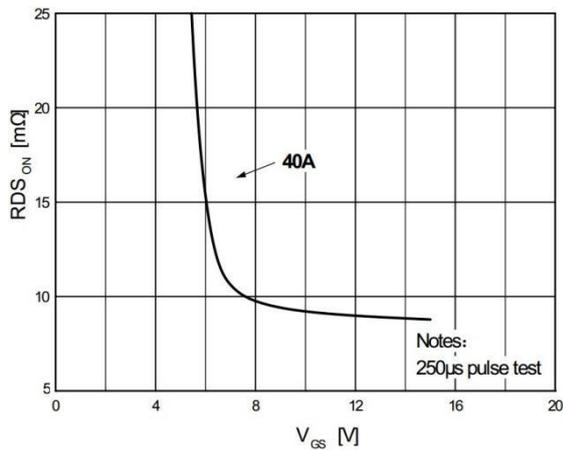
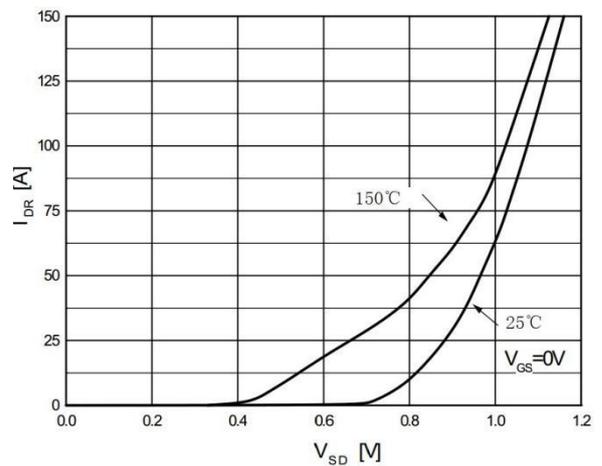
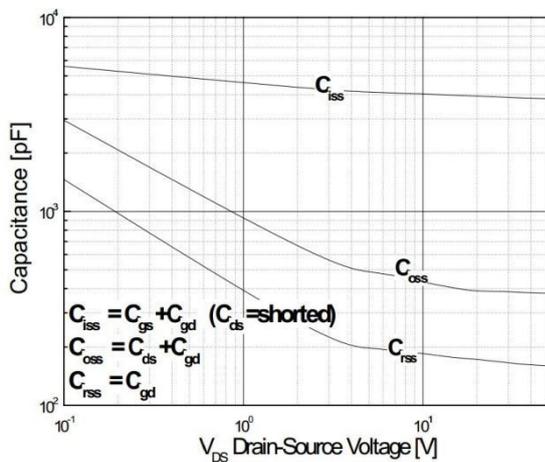
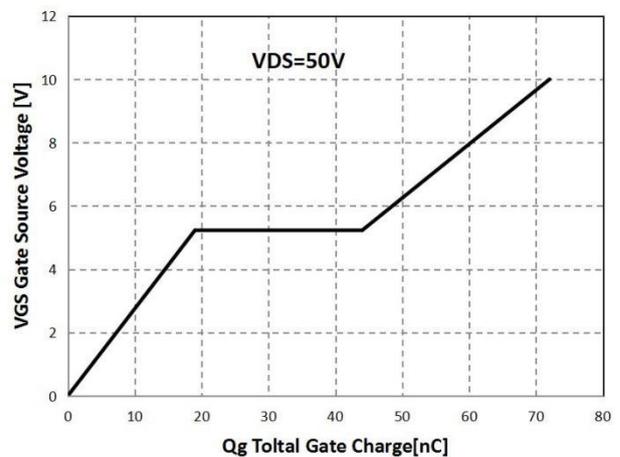
Electrical Characteristics (TA=25 °C Unless Otherwise Noted)

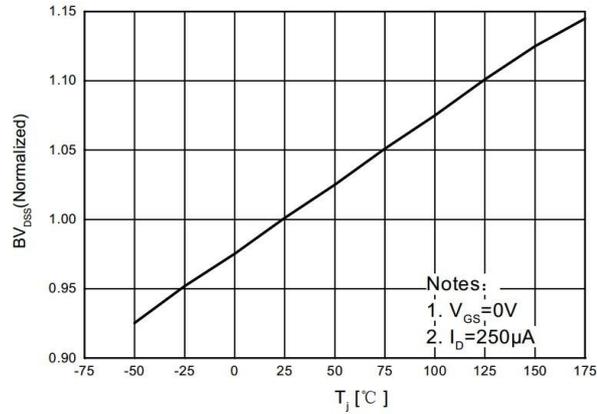
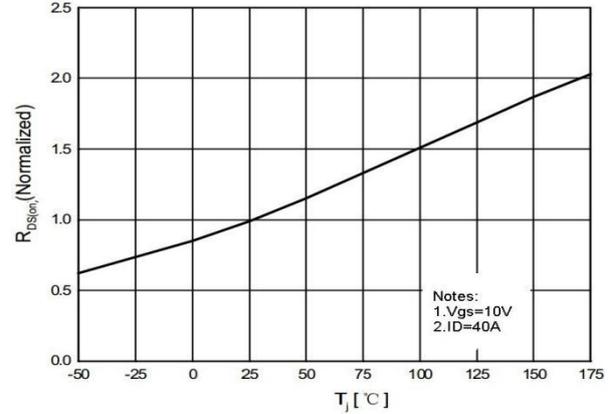
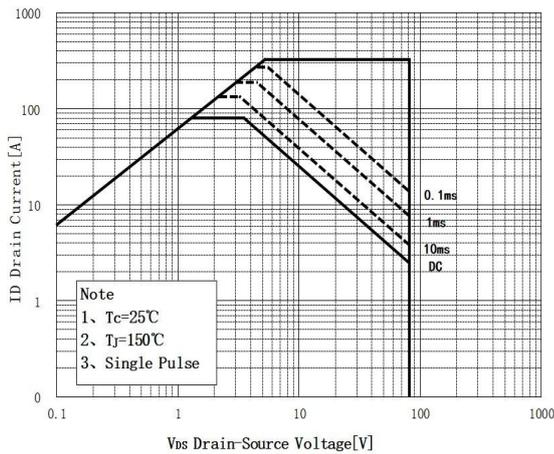
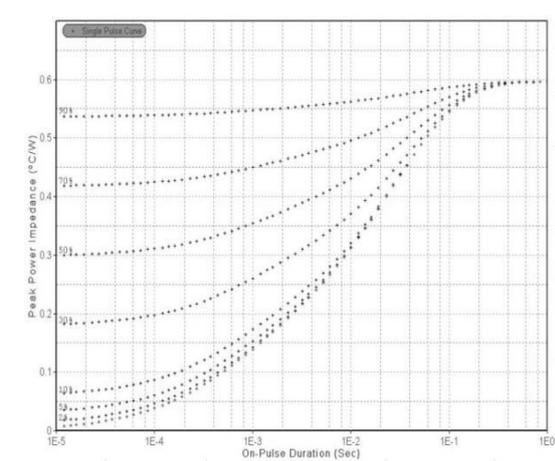
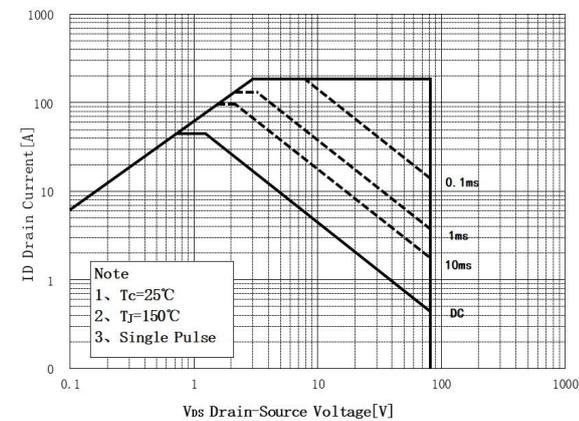
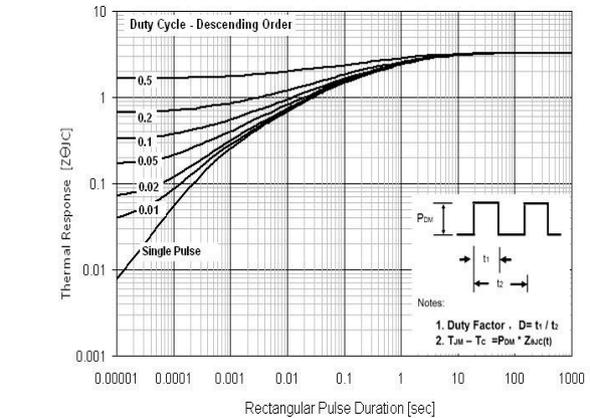
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS = 0 V, ID = 250 μ A	80	-	-	V
VGS(th)	Gate Threshold Voltage	VDS = VGS, IDS = 250 μ A	2.0	3.0	4.0	V
IDSS	Zero Gate Voltage Source Current	VDS = 160 V, VGS = 0 V	-	-	1	μ A
IGSS	Gate Leakage Current	VGS = \pm 20 V, VDS = 0 V	-	-	\pm 100	nA
RDS(ON) a	Drain-Source On-State Resistance	VGS = 10 V, ID = 1 A	-	9	12	m Ω
	Drain-Source On-State Resistance	VGS = 6 V, ID = 1 A	-	15	19	m Ω
Diode Characteristics						
VSDa	Diode Forward Voltage	ISD = 30A, VGS = 0 V	-	-	1.3	V
trr	Reverse Recovery Time	ISD = 30A, dISD/dt = 100 A/ μ s	-	46	-	nS
Qrr	Reverse Recovery Charge		-	56	-	nC
Dynamic Characteristics^b						
Ciss	Input Capacitance	VGS = 0 V, VDS = 25 V Frequency = 1 MHz	-	1460	-	pF
Coss	Output Capacitance		-	640	-	
Crss	Reverse Transfer Capacitance		-	35	-	
td(on)	Turn-on Delay Time	VDS = 40V, VGEN = 10 V, RG = 3.9 Ω , RL = 3.3 Ω , ID = 30 A	-	30	-	nS
tr	Turn-on Rise Time		-	81	-	
td(off)	Turn-off Delay Time		-	116	-	
tf	Turn-off Fall Time		-	62	-	
Gate Charge Characteristics^b						
Qg	Total Gate Charge	VGS = 10 V, VDS = 50 V, IDS = 30A	-	72	-	nC
Qgs	Gate-Source Charge		-	19	-	
Qgd	Gate-Drain Charge		-	26	-	

Notes :

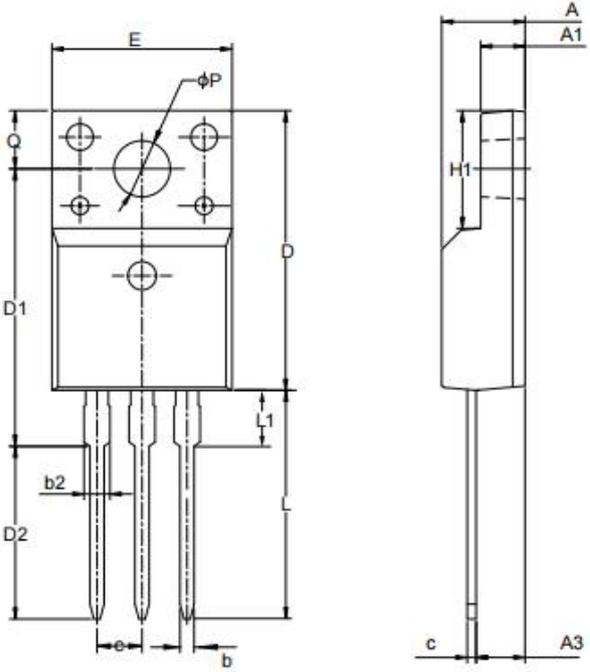
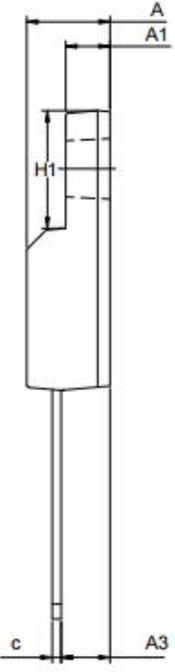
a : Pulse test ; pulse width \leq 300 μ s, duty cycle \leq 2%

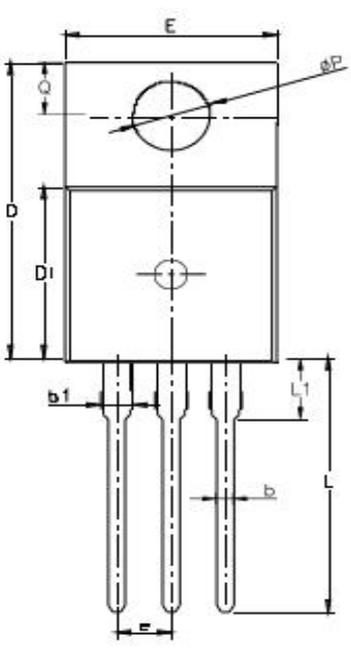
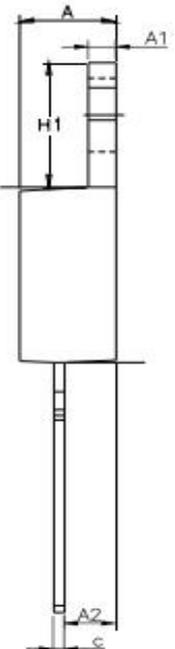
b : Guaranteed by design, not subject to production testing

Typical Characteristics
Fig1 Typical Output Characteristics, Tc=25°C

Fig2 Transfer Characteristics

Fig3 On-Resistance Variation vs. Drain Current and Gate Voltage

Fig4 Body Diode Forward Voltage Variation vs. Source Current and Temperature

Fig5 Capacitance Characteristics

Fig6 Gate Charge Characteristics


Typical Characteristics(cont.)
Fig7 Breakdown Voltage Variation vs. Temperature

Fig8 On-Resistance Variation vs. Temperature

Fig9 Maximum Safe Operating Area(TO-220/TO-252)

Fig10 Transient Thermal Response Curve (TO-220/TO-252)

Fig11 Maximum Safe Operating Area(TO-220F)

Fig12 Transient Thermal Response Curve (TO-220F)


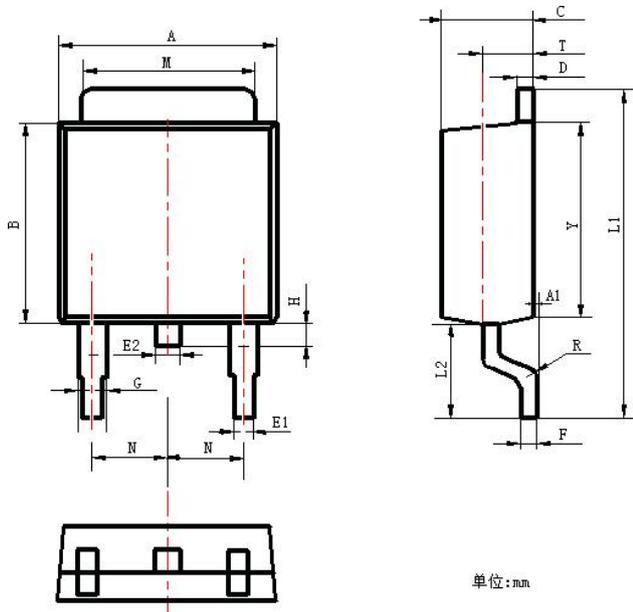
Package Dimensions

TO-220F-3L		单位: mm			
		Values(mm)			
		Items	MIN	NOM	MAX
		A	4.42	4.7	5.02
		A1	2.3	2.54	2.8
		A3	2.5	2.76	3.1
		b	0.7	0.8	0.9
		b2	--	--	1.47
		c	0.35	0.5	0.65
		D	15.25	15.87	16.25
		D1	15.3	15.75	16.3
		D2	9.3	9.8	10.3
		E	9.73	10.16	10.36
		e	2.54BSC		
		H1	6.4	6.68	7
		L	12.48	12.98	13.48
		L1	--	--	3.5
		øP	3	3.18	3.4
		Q	3.05	3.3	3.55

TO-220-3L		单位: mm			
		Values(mm)			
		Items	MIN	NOM	MAX
		A	4.3	4.5	4.7
		A1	1	1.3	1.5
		A2	1.8	2.4	2.8
		b	0.6	0.8	1
		b1	1	-	1.6
		c	0.3	-	0.7
		D	15.1	15.7	16.1
		D1	8.1	9.2	10
		F	9.6	9.9	10.4
		e	2.54BSC		
		H1	6.1	6.5	7
		L	12.6	13.08	13.6
		L1			3.95
		ΦP	3.4	3.7	3.9
		Q	2.6		3.2

Package Dimensions
TO-252-2L

单位: mm



单位: mm

Items	Values(mm)		
	MIN	NOM	MAX
A	6.3	6.5	6.9
A1	0	-	0.16
B	5.7	-	6.3
C	2.1	2.3	2.5
D	0.3	0.5	0.7
E1	0.6	0.65	0.9
E2	0.7	0.65	1
F	0.3	0.5	0.6
G	0.7	0.9	1.2
L1	9.6	10	10.5
L2	2.7	-	3.1
H	0.4	-	1
M	5.1	5.2	5.5
N	2.09	2.2	2.49
R	0.3		
T	1.4	-	1.6
Y	5.1	5.9	6.3